

N-channel 800 V, 2.1 Ω typ., 3 A MDmesh™ K5 Power MOSFET in a TO-220FP package

Datasheet - production data

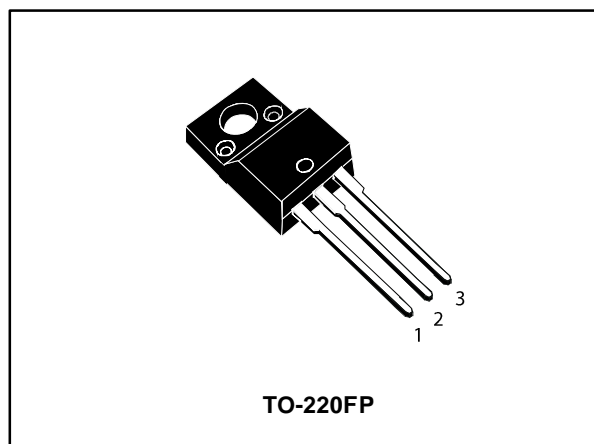
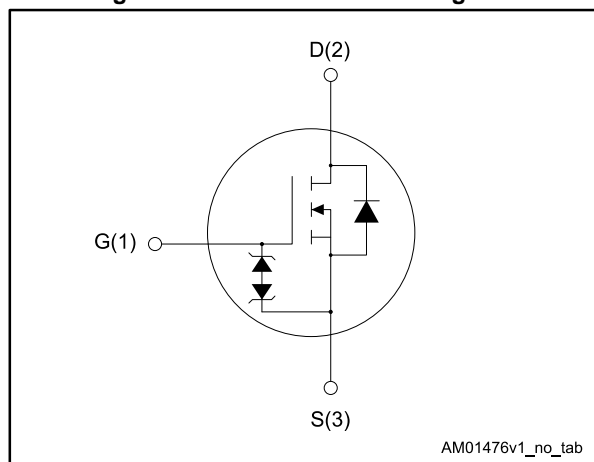


Figure 1: Internal schematic diagram



Features

Order code	V _{DS}	R _{DS(on)} max.	I _D
STF4LN80K5	800 V	2.6 Ω	3 A

- Industry's lowest R_{DS(on)}* area
- Industry's best FoM (figure of merit)
- Ultra low-gate charge
- 100% avalanche tested
- Zener-protected

Applications

- Switching applications

Description

This very high voltage N-channel Power MOSFET is designed using MDmesh™ K5 technology based on an innovative proprietary vertical structure. The result is a dramatic reduction in on-resistance and ultra-low gate charge for applications requiring superior power density and high efficiency.

Table 1: Device summary

Order code	Marking	Package	Packing
STF4LN80K5	4LN80K5	TO-220FP	Tube

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1 Electrical ratings

Table 2: Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{GS}	Gate-source voltage	± 30	V
$I_D^{(1)}$	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	3	A
$I_D^{(1)}$	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	1.9	A
$I_D^{(2)}$	Drain current pulsed	12	A
P_{TOT}	Total dissipation at $T_C = 25\text{ }^\circ\text{C}$	20	W
V_{iso}	Insulation withstand voltage (RMS) from all three leads to external heat sink. ($t = 1\text{ s}$; $T_C = 25\text{ }^\circ\text{C}$)	2500	V
$dv/dt^{(3)}$	Peak diode recovery voltage slope	15	V/ns
$dv/dt^{(4)}$	MOSFET dv/dt ruggedness	50	
T_j	Operating junction temperature range	- 55 to 150	$^\circ\text{C}$
T_{stg}	Storage temperature range		

Notes:

(1)Limited by maximum junction temperature.

(2)Pulse width limited by safe operating area

(3) $I_{SD} \leq 3\text{ A}$, $di/dt \leq 100\text{ A}/\mu\text{s}$; $V_{DS\text{ peak}} \leq V_{(BR)DSS}$, $V_{DD} = 400\text{ V}$.

(4) $V_{DS} \leq 640\text{ V}$

Table 3: Thermal data

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case	6.25	$^\circ\text{C}/\text{W}$
$R_{thj-amb}$	Thermal resistance junction-ambient	62.5	$^\circ\text{C}/\text{W}$

Table 4: Avalanche characteristics

Symbol	Parameter	Value	Unit
I_{AR}	Avalanche current, repetitive or not repetitive (pulse width limited by T_{jmax})	0.8	A
E_{AS}	Single pulse avalanche energy (starting $T_j = 25\text{ }^\circ\text{C}$, $I_D = I_{AR}$, $V_{DD} = 50\text{ V}$)	160	mJ

2 Electrical characteristics

$T_C = 25\text{ °C}$ unless otherwise specified

Table 5: On/off-state

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$V_{GS} = 0\text{ V}$, $I_D = 1\text{ mA}$	800			V
I_{DSS}	Zero gate voltage drain current	$V_{GS} = 0\text{ V}$, $V_{DS} = 800\text{ V}$			1	μA
		$V_{GS} = 0\text{ V}$, $V_{DS} = 800\text{ V}$ $T_C = 125\text{ °C}^{(1)}$			50	μA
I_{GSS}	Gate body leakage current	$V_{DS} = 0\text{ V}$, $V_{GS} = \pm 20\text{ V}$			± 10	μA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$, $I_D = 100\text{ }\mu\text{A}$	3	4	5	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10\text{ V}$, $I_D = 1\text{ A}$		2.1	2.6	Ω

Notes:

⁽¹⁾ Defined by design, not subject to production test.

Table 6: Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	$V_{DS} = 100\text{ V}$, $f = 1\text{ MHz}$, $V_{GS} = 0\text{ V}$	-	122	-	pF
C_{oss}	Output capacitance		-	11	-	pF
C_{rss}	Reverse transfer capacitance		-	0.3	-	pF
$C_{o(tr)}^{(1)}$	Equivalent capacitance time related	$V_{DS} = 0\text{ to }640\text{ V}$, $V_{GS} = 0\text{ V}$	-	23	-	pF
$C_{o(er)}^{(2)}$	Equivalent capacitance energy related		-	9	-	pF
R_g	Intrinsic gate resistance	$f = 1\text{ MHz}$, $I_D = 0\text{ A}$	-	18	-	Ω
Q_g	Total gate charge	$V_{DD} = 640\text{ V}$, $I_D = 2.5\text{ A}$ $V_{GS} = 10\text{ V}$, see Figure 15: "Test circuit for gate charge behavior"	-	3.7	-	nC
Q_{gs}	Gate-source charge		-	1	-	nC
Q_{gd}	Gate-drain charge		-	2.2	-	nC

Notes:

⁽¹⁾ Time related is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS} .

⁽²⁾ Energy related is defined as a constant equivalent capacitance giving the same stored energy as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS} .

Table 7: Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 400\text{ V}$, $I_D = 1.25\text{ A}$, $R_G = 4.7\ \Omega$ $V_{GS} = 10\text{ V}$, see Figure 14: "Test circuit for resistive load switching times" and Figure 19: "Switching time waveform"	-	7	-	ns
t_r	Rise time		-	9	-	ns
$t_{d(off)}$	Turn-off delay time		-	31	-	ns
t_f	Fall time		-	25	-	ns

Table 8: Source-drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-		3	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		12	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 2.5\text{ A}$, $V_{GS} = 0\text{ V}$	-		1.5	V
t_{rr}	Reverse recovery time	$I_{SD} = 2.5\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$, $V_{DD} = 60\text{ V}$, see Figure 16: "Test circuit for inductive load switching and diode recovery times"	-	230		ns
Q_{rr}	Reverse recovery charge		-	1.04		μC
I_{RRM}	Reverse recovery current		-	9		A
t_{rr}	Reverse recovery time	$I_{SD} = 2.5\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$, $V_{DD} = 60\text{ V}$, $T_j = 150\text{ }^\circ\text{C}$, see Figure 16: "Test circuit for inductive load switching and diode recovery times"	-	368		ns
Q_{rr}	Reverse recovery charge		-	1.53		μC
I_{RRM}	Reverse recovery current		-	8		A

Notes:

(1)Pulse width limited by safe operating area

(2)Pulsed: pulse duration = 300 μs , duty cycle 1.5%

Table 9: Gate-source Zener diode

Symbol	Parameter	Test conditions	Min	Typ.	Max	Unit
$V_{(BR)GSO}$	Gate-source breakdown voltage	$I_{GS} = \pm 1\text{ mA}$, $I_D = 0\text{ A}$	30	-	-	V

The built-in back-to-back Zener diodes are specifically designed to enhance the ESD performance of the device. The Zener voltage facilitates efficient and cost-effective device integrity protection, thus eliminating the need for additional external componentry.

2.1 Electrical characteristics (curves)

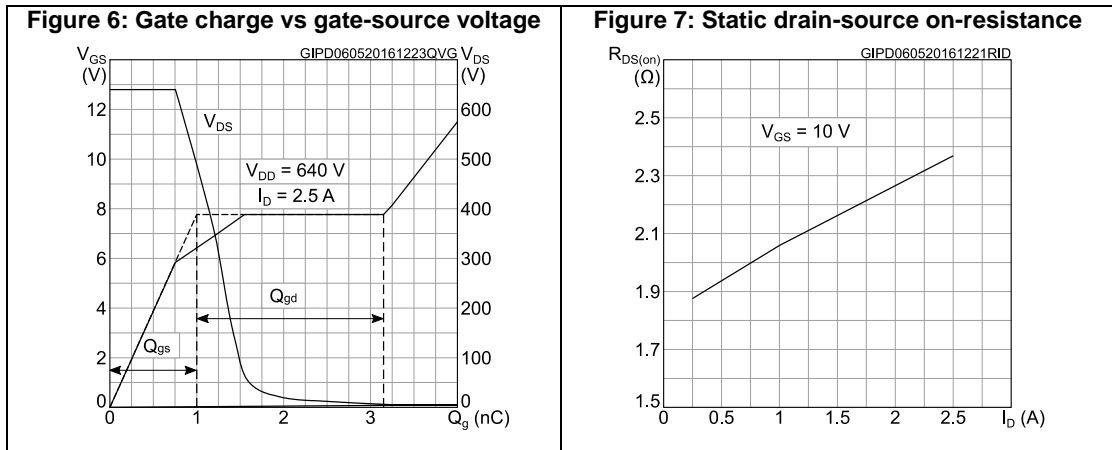
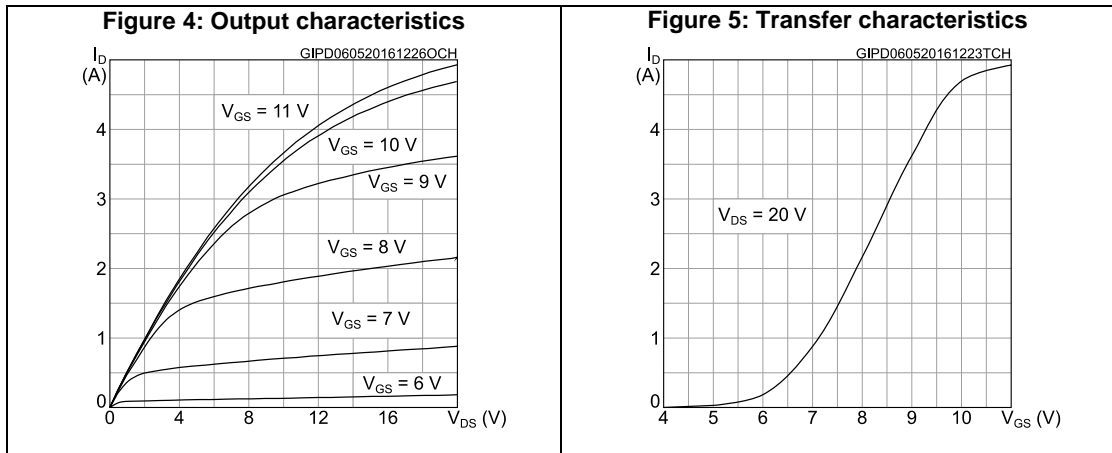
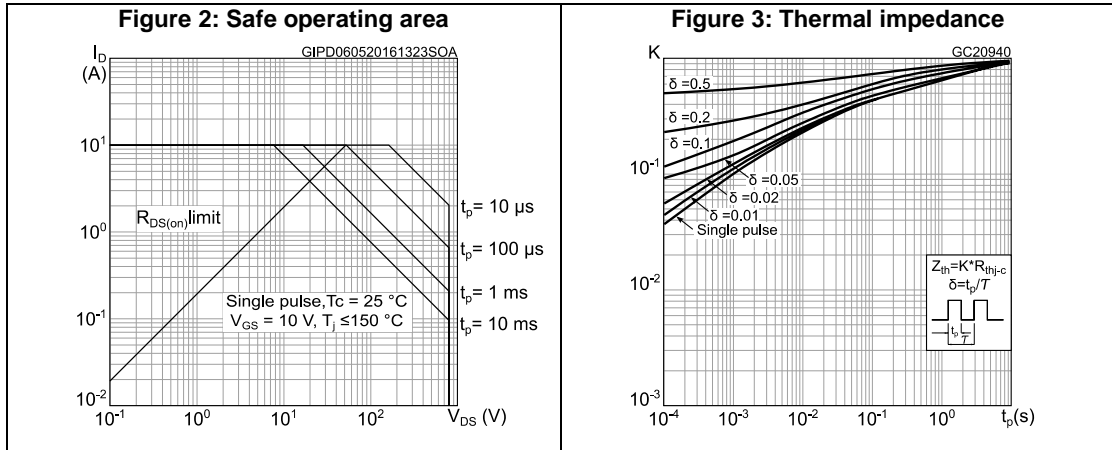


Figure 8: Capacitance variations

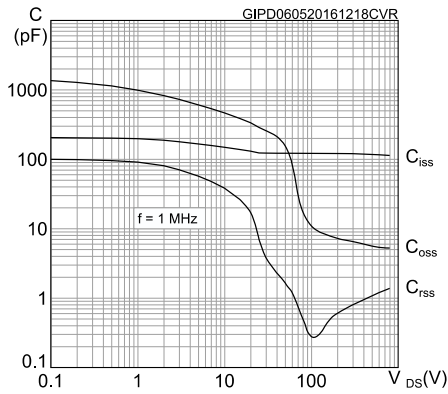


Figure 9: Normalized gate threshold voltage vs temperature

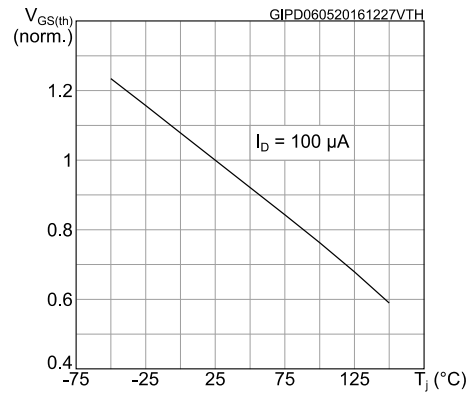


Figure 10: Normalized on-resistance vs temperature

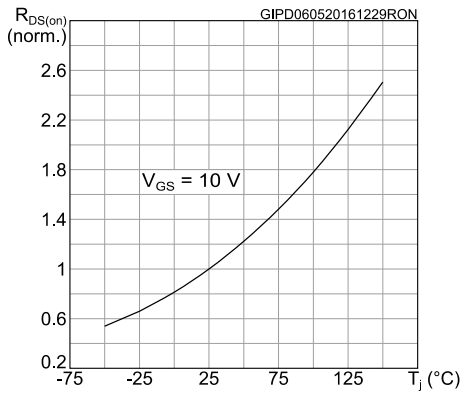


Figure 11: Normalized V_{(BR)DSS} vs temperature

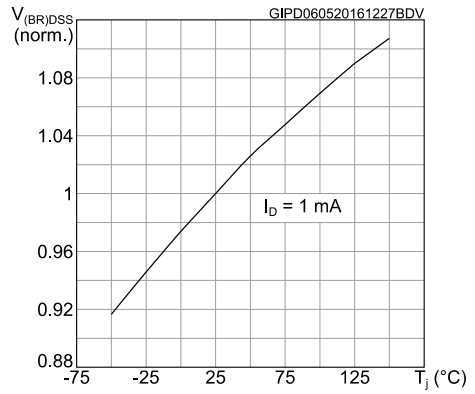


Figure 12: Maximum avalanche energy vs starting T_J

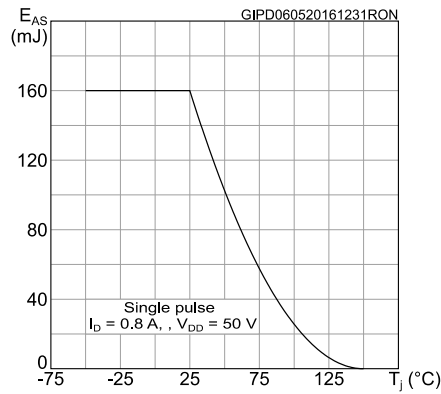
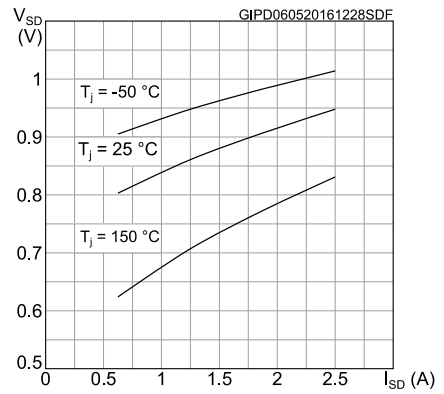
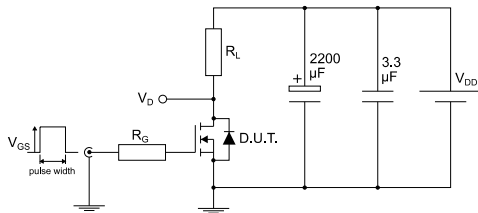


Figure 13: Source-drain diode forward characteristics



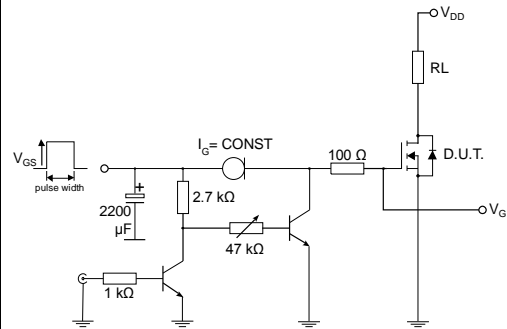
3 Test circuits

Figure 14: Test circuit for resistive load switching times



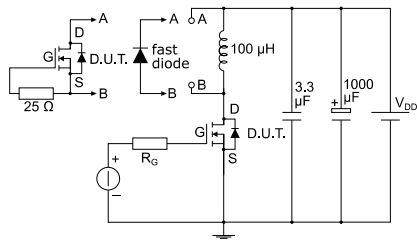
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Figure 15: Test circuit for gate charge behavior



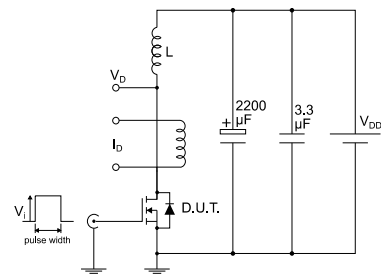
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Figure 16: Test circuit for inductive load switching and diode recovery times



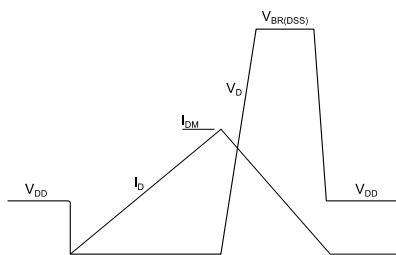
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Figure 17: Unclamped inductive load test circuit



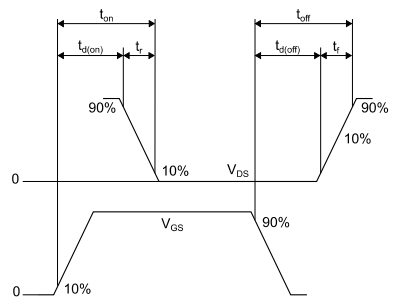
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Figure 18: Unclamped inductive waveform



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Figure 19: Switching time waveform



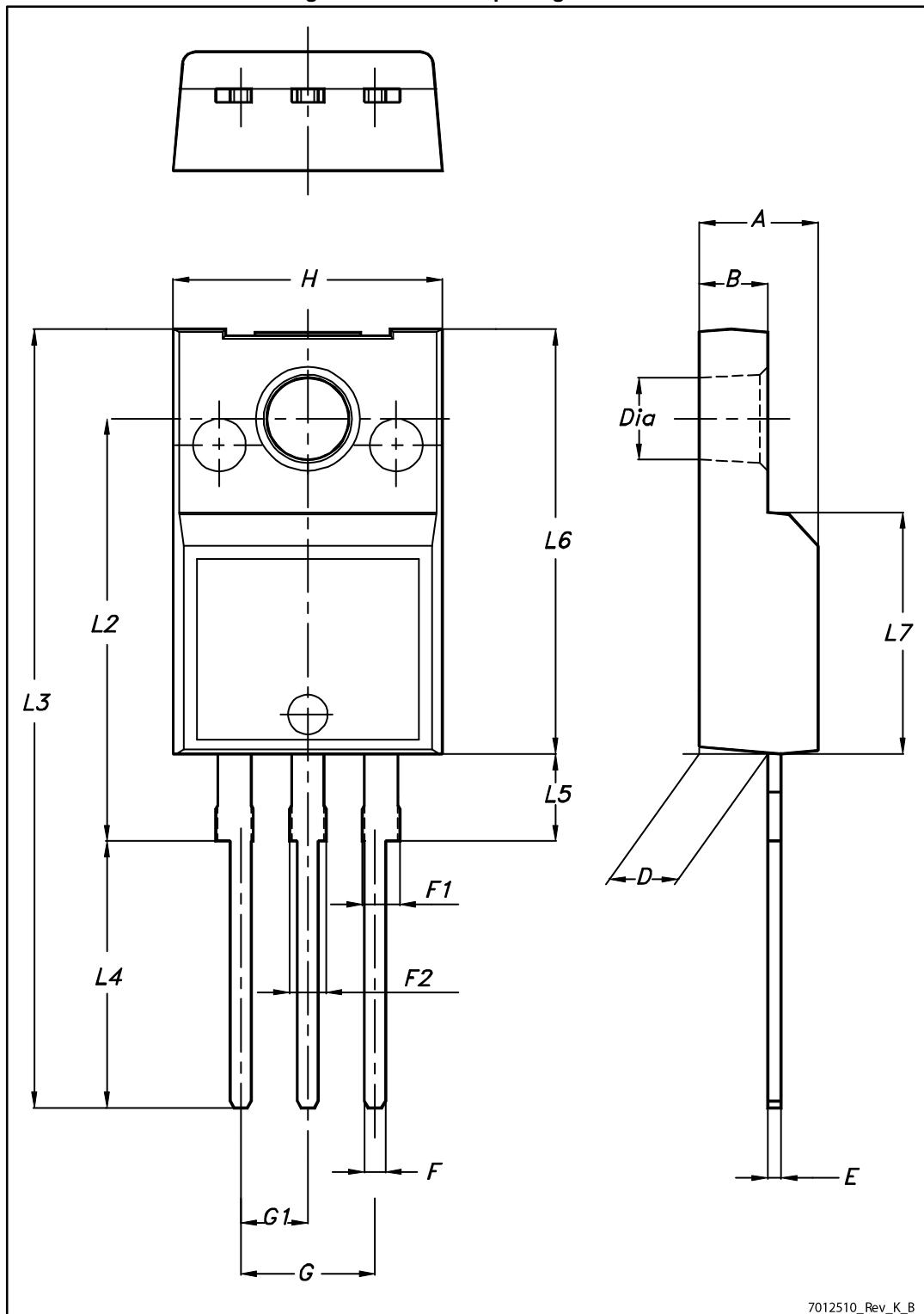
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4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK® is an ST trademark.

4.1 TO-220FP package information

Figure 20: TO-220FP package outline



7012510_Rev_K_B

Table 10: TO-220FP package mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.4		4.6
B	2.5		2.7
D	2.5		2.75
E	0.45		0.7
F	0.75		1
F1	1.15		1.70
F2	1.15		1.70
G	4.95		5.2
G1	2.4		2.7
H	10		10.4
L2		16	
L3	28.6		30.6
L4	9.8		10.6
L5	2.9		3.6
L6	15.9		16.4
L7	9		9.3
Dia	3		3.2

5 Revision history

Table 11: Document revision history

Date	Revision	Changes
04-Jun-2015	1	First release.
18-May-2016	2	Document status promoted from preliminary data to production data. Updated <i>Figure 1: "Internal schematic diagram"</i> . Updated <i>Section 1: "Electrical ratings"</i> , <i>Section 2: "Electrical characteristics"</i> . Added <i>Section 2.1: "Electrical characteristics (curves)"</i> . Updated <i>Section 3: "Test circuits"</i> . Minor text changes.

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